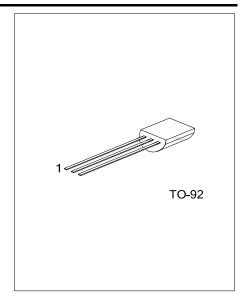
03N50-KW Preliminary Power MOSFET

# 0.3A, 500V N-CHANNEL POWER MOSFET

#### **■** DESCRIPTION

The UTC **03N50-KW** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

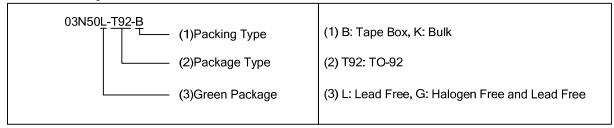


#### **■ FEATURES**

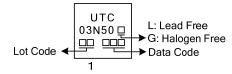
#### **■ ORDERING INFORMATION**

Ordering Number		Dackago	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
03N50L-T92-B	03N50G-T92-B	TO-92	G	D	S	Tape Box	
03N50L-T92-K	03N50G-T92-K	TO-92	G	D	S	Bulk	

Note: Pin Assignment: G: Gate D: Drain S: Source



### **■ MARKING**



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<sup>\*</sup>  $R_{DS(on)}$  < 15 $\Omega$  @  $V_{GS}$ =10V,  $I_{D}$ =0.15A

<sup>\*</sup> High breakdown voltage

## **ABSOLUTE MAXIMUM RATINGS** (T<sub>C</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	500	V
Gate-Source Voltage		$V_{GSS}$	±30	V
Drain Current	Continuous	I <sub>D</sub>	0.3	Α
	Pulsed	I <sub>DM</sub>	1.2	Α
Avalanche Current		I <sub>AR</sub>	0.3	Α
Power Dissipation		$P_{D}$	425	mW
Junction Temperature		$T_J$	150	°C
Storage Temperature Range		T <sub>STG</sub>	-55 ~ <b>+</b> 150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	$\theta_{JA}$	180	°C/W	
Junction to Case	θ <sub>JC</sub>	38	°C/W	

# ELECTRICAL CHARACTERISTICS (T<sub>C</sub> =25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT	
OFF CHARACTERISTICS			•	•	•			
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	500			V	
Drain-Source Leakage Current		I <sub>DSS</sub>	V <sub>DS</sub> =500V, V <sub>GS</sub> =0V			10	μΑ	
Gate-Source Leakage Current	Forward	_	V <sub>GS</sub> =+30V, V <sub>DS</sub> =0V			+100	nA	
	Reverse	I <sub>GSS</sub>	V <sub>GS</sub> =-30V, V <sub>DS</sub> =0V			-100	nA	
ON CHARACTERISTICS								
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu A$	2.0		4.0	V	
Static Drain-Source On-State Resistance		R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =0.15A			15	Ω	
DYNAMIC PARAMETERS								
Input Capacitance		C <sub>ISS</sub>			74		рF	
Output Capacitance		Coss	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1.0MHz		12.7		рF	
Reverse Transfer Capacitance		C <sub>RSS</sub>	]		4.6		рF	
SWITCHING PARAMETERS								
Total Gate Charge		$Q_G$	-\/ 50\/ \/ 10\/ \		7.84		nC	
Gate to Source Charge		$Q_{GS}$	$V_{DS}$ = 50V, $V_{GS}$ = 10V, $I_{D}$ = 0.3A, $I_{D}$ =100 $\mu$ A (Note 1, 2)		0.94		nC	
Gate to Drain Charge		$Q_GD$	T <sub>D</sub> = τουμΑ (Note 1, 2)		0.55		nC	
Turn-ON Delay Time		t <sub>D(ON)</sub>			50		ns	
Rise Time		t <sub>R</sub>	$V_{DS}$ = 30V, $V_{GS}$ = 10V, $I_{D}$ = 0.3A,		17.8		ns	
Turn-OFF Delay Time		t <sub>D(OFF)</sub>	$R_G = 25\Omega \text{ (Note 1, 2)}$		44		ns	
Fall-Time		t <sub>F</sub>			28.2		ns	
SOURCE- DRAIN DIODE RATIF	NGS AND C	HARACTERI	STICS					
Maximum Body-Diode Continuous Current		Is				0.3	Α	
Maximum Body-Diode Pulsed Current		I <sub>SM</sub>				1.2	Α	
Drain-Source Diode Forward Voltage		V <sub>SD</sub>	I <sub>S</sub> =0.3A, V <sub>GS</sub> =0V			1.4	V	
Notes: 1. Pulse Test: Pulse width	າ ≤ 300µs, D	uty cycle ≤ 2°	%.	\				
2. Essentially independer	nt of operatin	g temperatur	I <sub>S</sub> =0.3A, V <sub>GS</sub> =0V %. e.	**				
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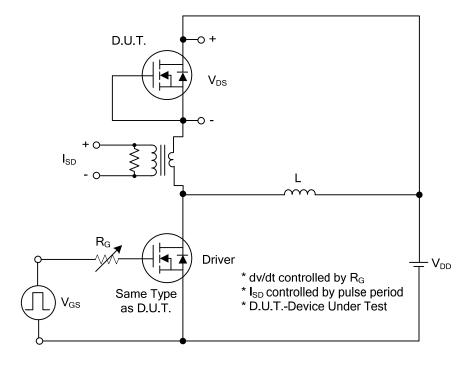
Notes: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle ≤ 2%.



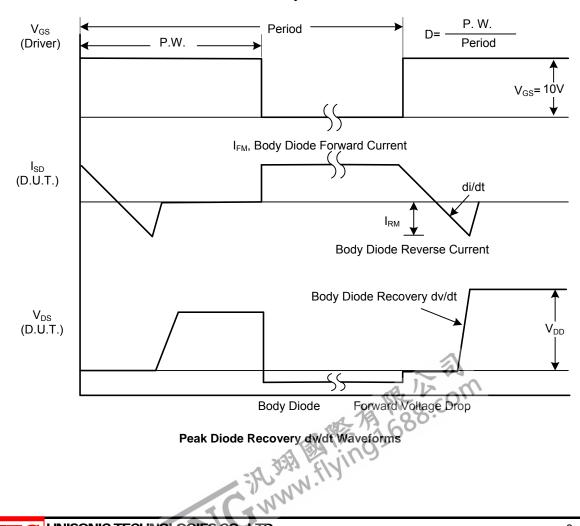
<sup>2.</sup> Repetitive Rating: Pulse width limited by maximum junction temperature

<sup>2.</sup> Essentially independent of operating temperature.

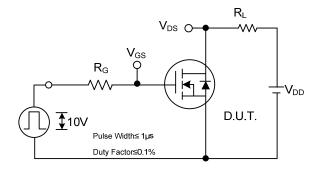
# **TEST CIRCUITS AND WAVEFORMS**

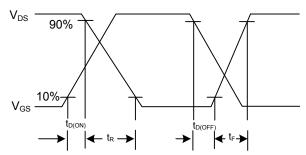


#### Peak Diode Recovery dv/dt Test Circuit



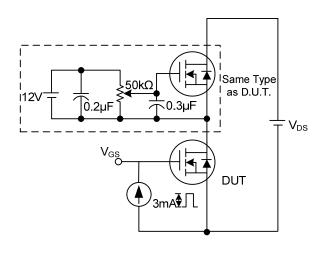
# **TEST CIRCUITS AND WAVEFORMS (Cont.)**

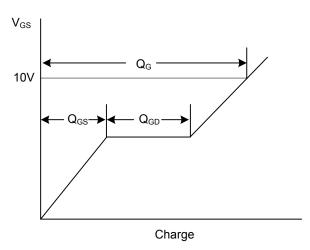




**Switching Test Circuit** 

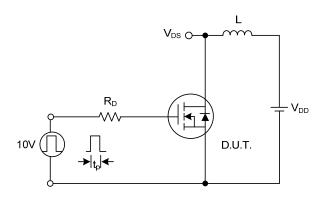
**Switching Waveforms** 

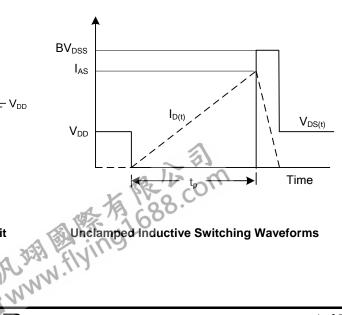




**Gate Charge Test Circuit** 

**Gate Charge Waveform** 





**Unclamped Inductive Switching Test Circuit** 

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